

1. General description

Planar passivated high commutation three quadrant triac in a SOT223 surface mountable plastic package intended for use in circuits where high static and dynamic dV/dt and high dI/dt can occur. This triac will commute the full rated RMS current at the maximum rated junction temperature without the aid of a snubber.

2. Applications

- General purpose motor controls
- Home appliances
- Rectifier-fed DC inductive loads e.g. DC motors and solenoids

3. Quick reference data

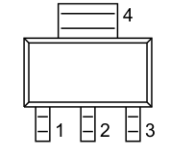
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	600	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{sp} \leq 108\text{ °C}$; Fig. 1 ; Fig. 2 ; Fig. 3	-	-	1	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 16.7\text{ ms}$	-	-	11	A
		full sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 20\text{ ms}$; Fig. 4 ; Fig. 5	-	-	10	A
T_j	junction temperature		-	-	125	°C
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ °C}$; Fig. 9	-	-	50	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ °C}$; Fig. 9	-	-	50	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ °C}$; Fig. 9	-	-	50	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_j = 25\text{ °C}$; Fig. 11	-	-	30	mA
V_T	on-state voltage	$I_T = 2\text{ A}$; $T_j = 25\text{ °C}$; Fig. 12	-	1.2	1.5	V
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 402\text{ V}$; $T_j = 125\text{ °C}$; (67% of V_{DRM}); exponential waveform; gate open circuit	1000	-	-	V/ μ s

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
di_{com}/dt	rate of change of commutating current	$V_D = 400\text{ V}$; $T_j = 125\text{ }^{\circ}\text{C}$; $I_{T(RMS)} = 1\text{ A}$; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$; (snubberless condition); gate open circuit		6	-	-	A/ms

4. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	 SC-73 (SOT223)	 sym051
2	T2	main terminal 2		
3	G	gate		
4	mb	mounting base; connected to T2		

5. Ordering information

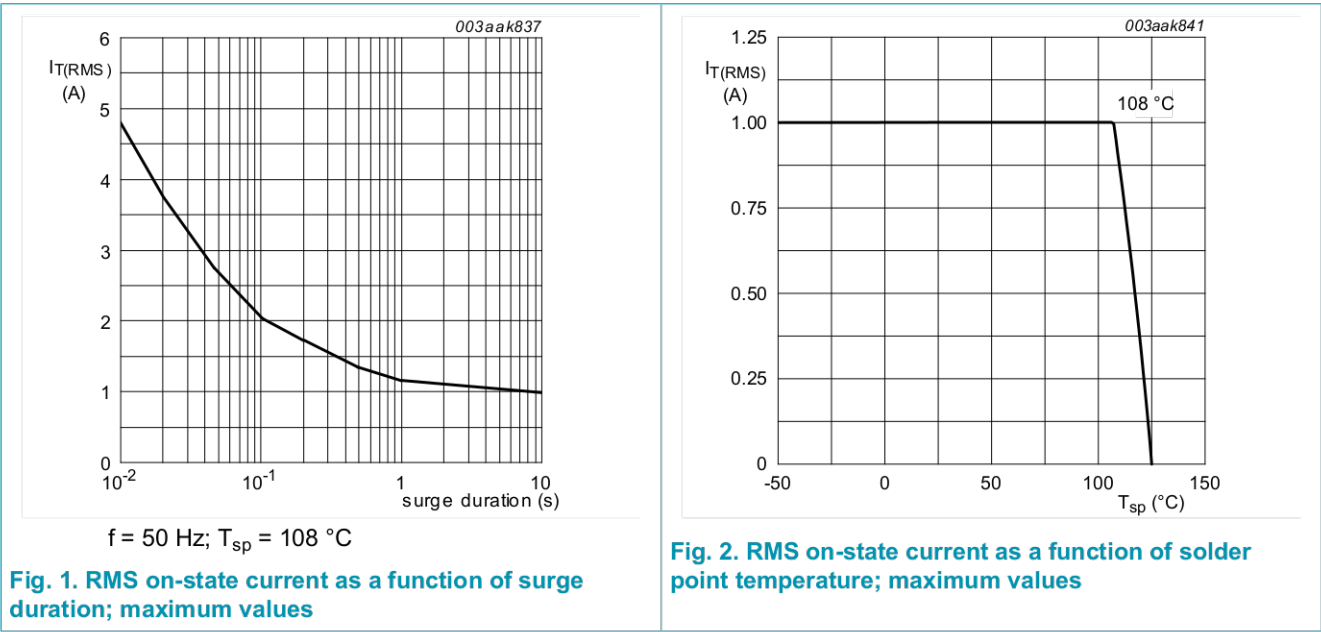
Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BTA204W-600B	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223

6. Limiting values

Table 4. Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DRM}	repetitive peak off-state voltage			-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{sp} ≤ 108 °C; Fig. 1; Fig. 2; Fig. 3		-	1	A
I _{TSM}	non-repetitive peak on-state current	full sine wave; T _{j(init)} = 25 °C; t _p = 16.7 ms		-	11	A
		full sine wave; T _{j(init)} = 25 °C; t _p = 20 ms; Fig. 4; Fig. 5		-	10	A
I ² t	I ² t for fusing	t _p = 10 ms; SIN		-	0.5	A ² s
dI _T /dt	rate of rise of on-state current	I _G = 0.2 A		-	100	A/μs
I _{GM}	peak gate current			-	2	A
P _{GM}	peak gate power			-	5	W
P _{G(AV)}	average gate power	over any 20ms period		-	0.5	W
T _{stg}	storage temperature			-40	150	°C
T _j	junction temperature			-	125	°C



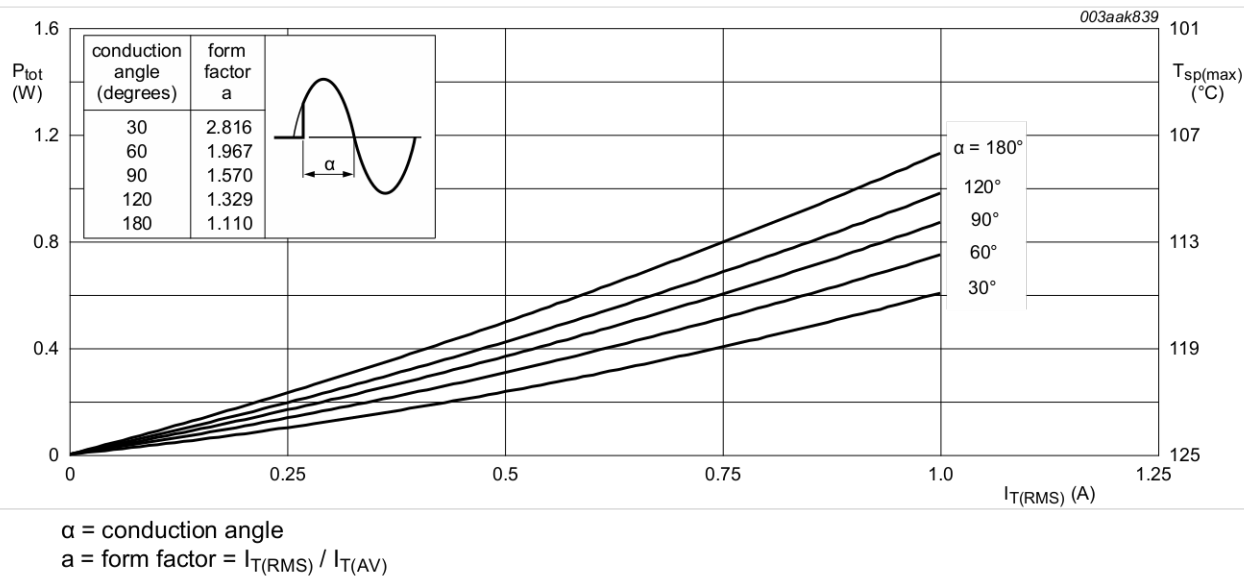


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

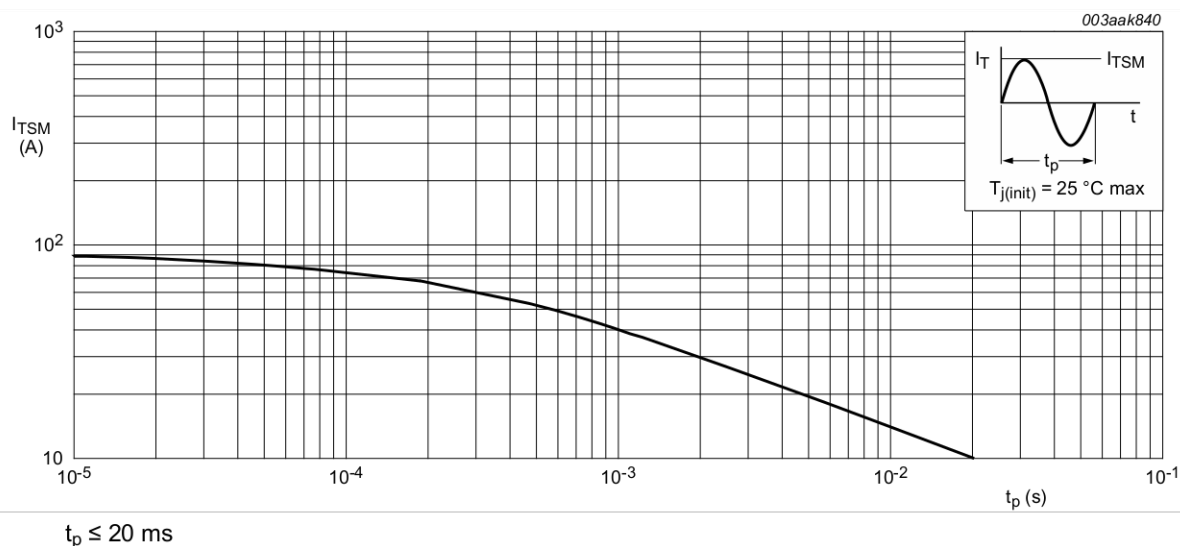
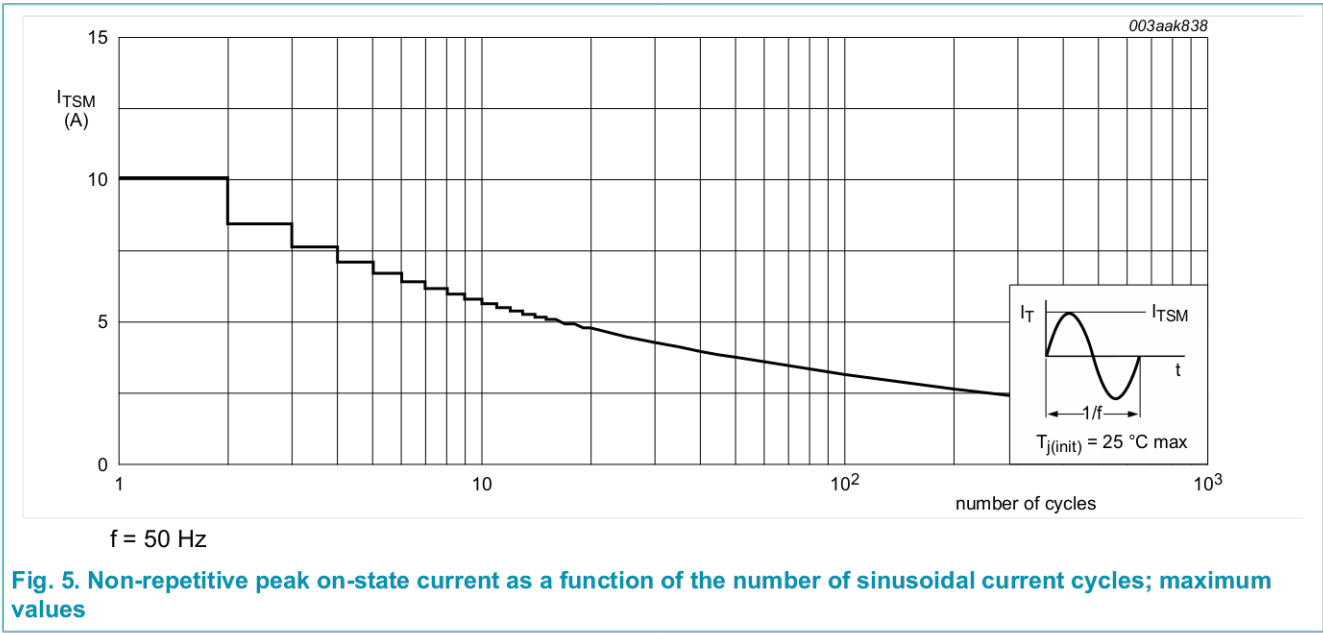


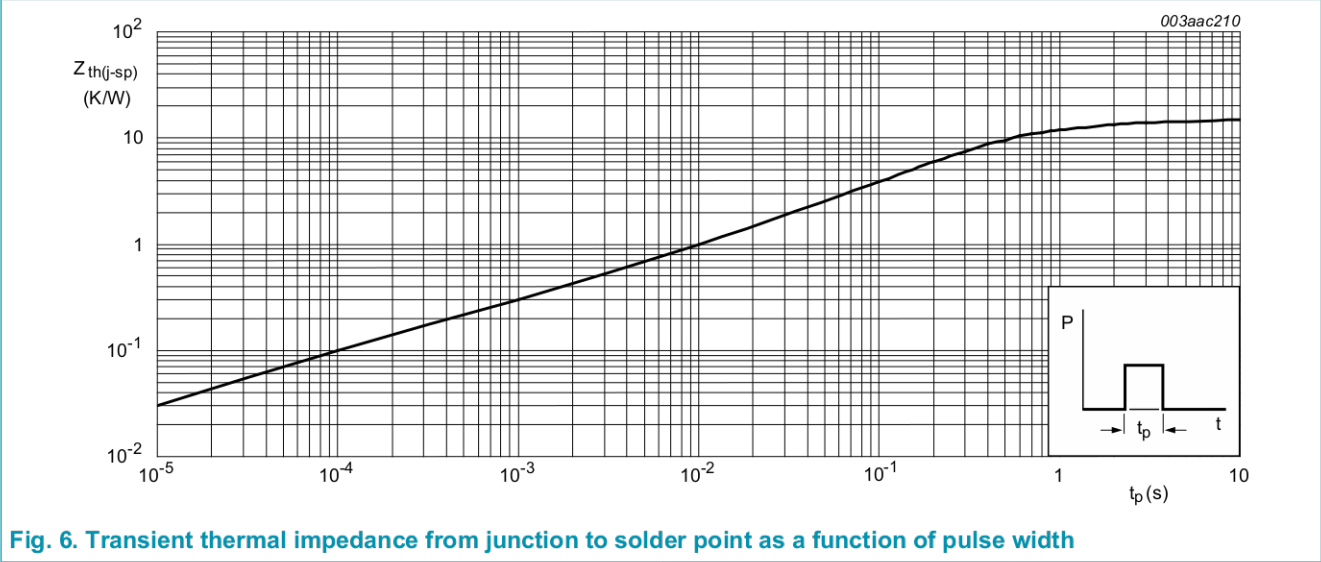
Fig. 4. Non-repetitive peak on-state current as a function of pulse width; maximum values

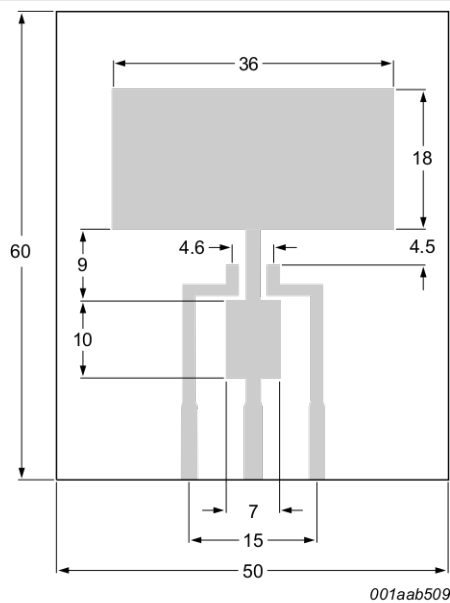


7. Thermal characteristics

Table 5. Thermal characteristics

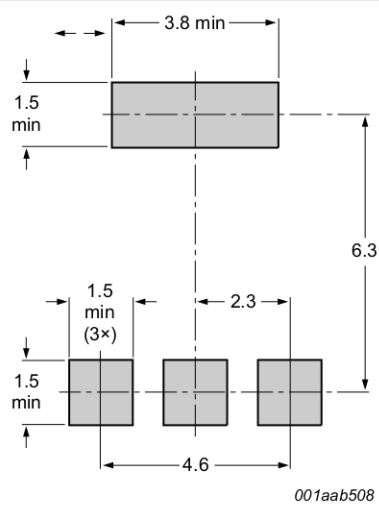
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	full cycle and half cycle; Fig. 6		-	-	15	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	printed circuit board mounted: minimum pad area; Fig. 7		-	70	-	K/W
		printed circuit board mounted: minimum footprint; Fig. 8		-	156	-	K/W





All dimensions are in mm
Printed circuit board:
FR4 epoxy glass (1.6 mm thick), copper laminate
(35 um thick)

Fig. 7. Printed circuit board pad area: SOT223



All dimensions are in mm

Fig. 8. Minimum footprint SOT223

8. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ }^\circ\text{C}$; Fig. 9		-	-	50	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ }^\circ\text{C}$; Fig. 9		-	-	50	mA
		$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ }^\circ\text{C}$; Fig. 9		-	-	50	mA
I_L	latching current	$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G-; $T_j = 25\text{ }^\circ\text{C}$; Fig. 10		-	-	30	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2+ G+; $T_j = 25\text{ }^\circ\text{C}$; Fig. 10		-	-	45	mA
		$V_D = 12\text{ V}$; $I_G = 0.1\text{ A}$; T2- G-; $T_j = 25\text{ }^\circ\text{C}$; Fig. 10		-	-	30	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 11		-	-	30	mA
V_T	on-state voltage	$I_T = 2\text{ A}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 12		-	1.2	1.5	V
V_{GT}	gate trigger voltage	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 13		-	0.7	1	V
		$V_D = 400\text{ V}$; $I_T = 0.1\text{ A}$; $T_j = 125\text{ }^\circ\text{C}$; Fig. 13		0.25	0.4	-	V
I_D	off-state current	$V_D = 600\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$		-	0.1	0.5	mA
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 402\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$; (67% of V_{DRM}); exponential waveform; gate open circuit		1000	-	-	V/ μs
dI_{com}/dt	rate of change of commutating current	$V_D = 400\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$; $I_{T(RMS)} = 1\text{ A}$; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$; (snubberless condition); gate open circuit		6	-	-	A/ms

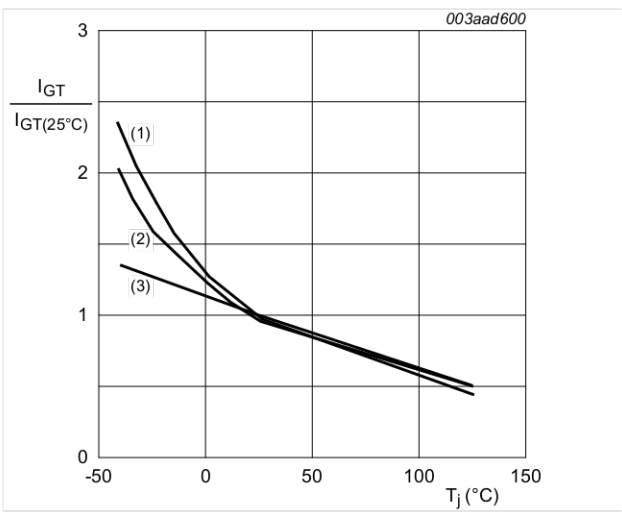


Fig. 9. Normalized gate trigger current as a function of junction temperature

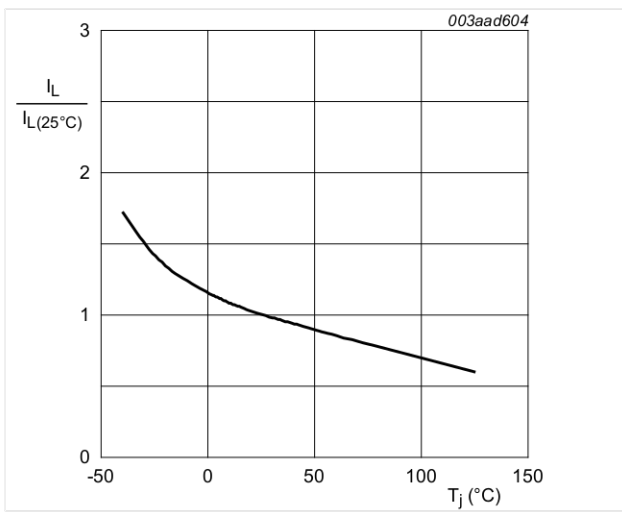


Fig. 10. Normalized latching current as a function of junction temperature

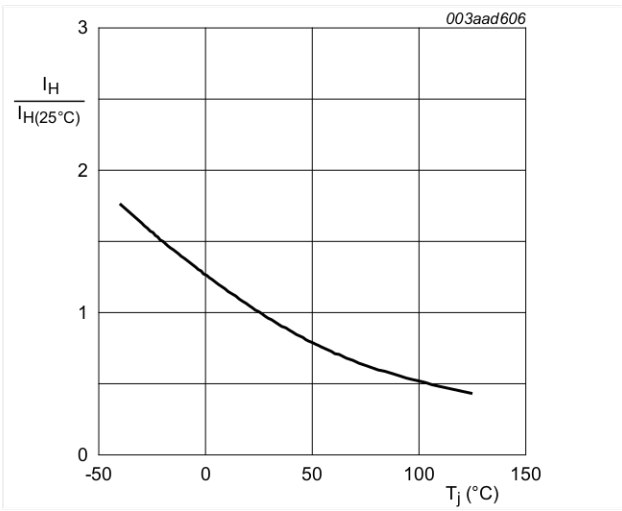


Fig. 11. Normalized holding current as a function of junction temperature

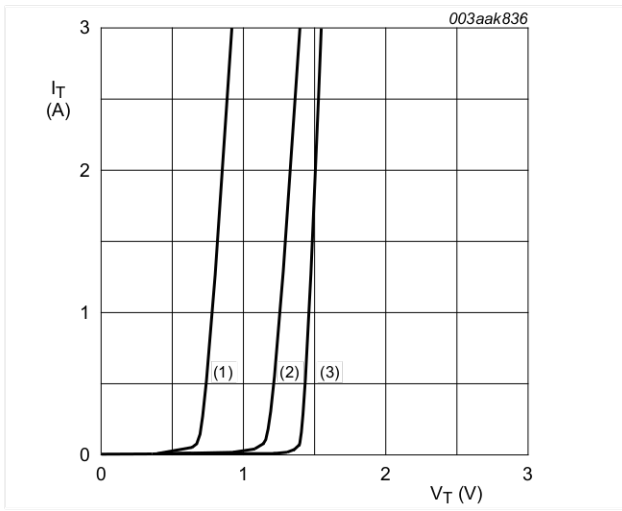


Fig. 12. On-state current as a function of on-state voltage

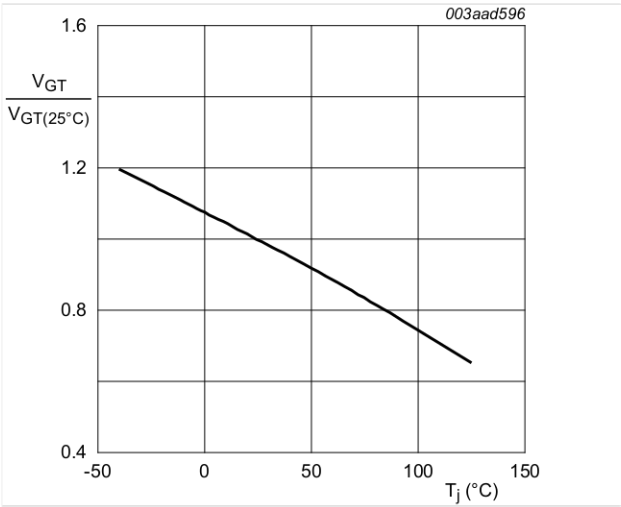
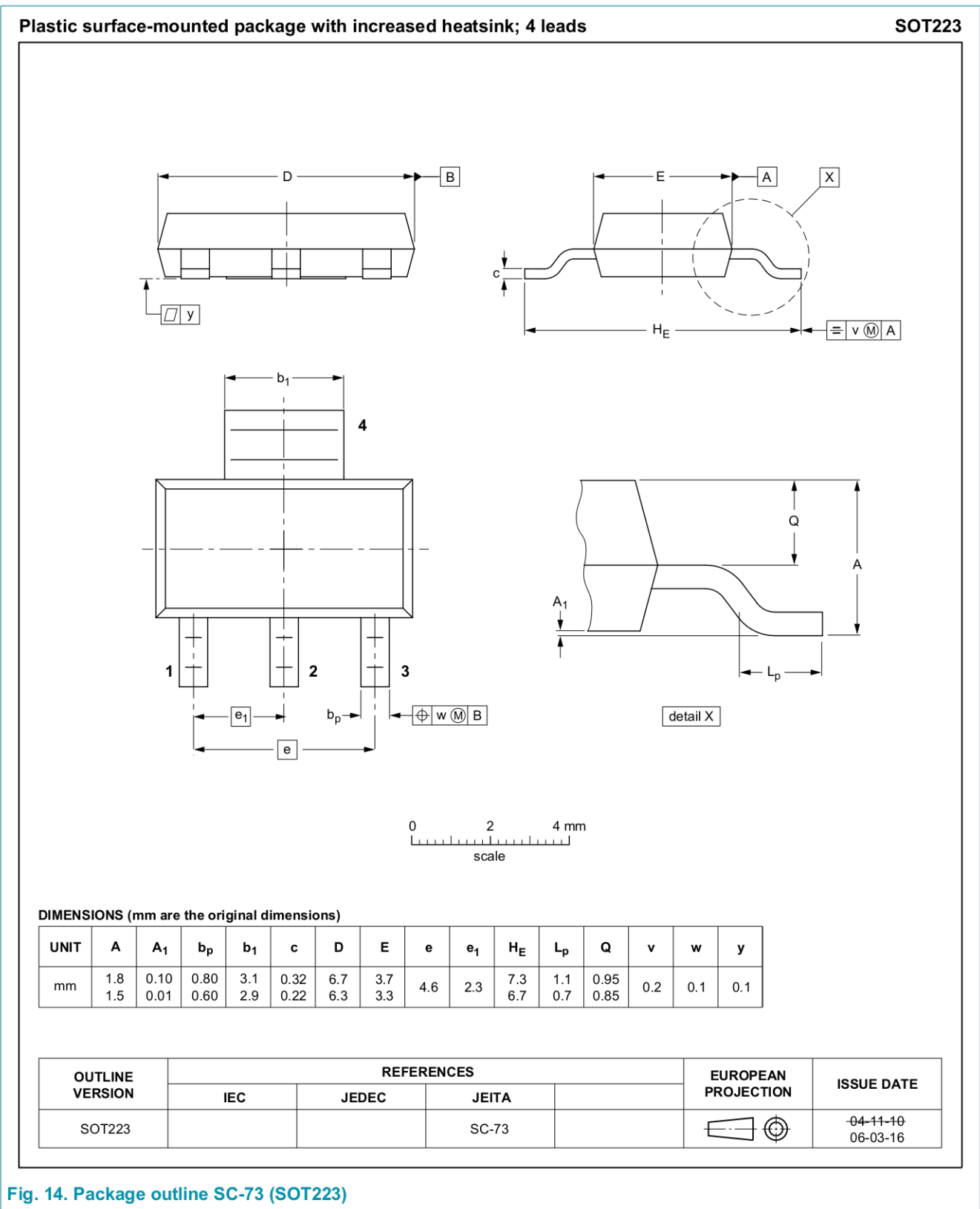


Fig. 13. Normalized gate trigger voltage as a function of junction temperature

9. Package outline



10. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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